SN74LV1T125, 具有三态输出的单电源单缓冲器门 CMOS 逻辑电平转换器

1 特性

- 电压为 5.0/3.3/2.5/1.8V 的单电源电压转换器 V_{CC}
- 1.8V 至 5.5V 的工作电压范围
- 上行转换
 - 1.8V V_{CC} 时,1.2V⁽¹⁾ 至 1.8V
 - 2.5V V_{CC} 时,1.5V⁽¹⁾ 至 2.5V
 - 3.3V V_{CC} 时,1.8V⁽¹⁾ 至 3.3V
 - 5.0V V_{CC} 时,3.3V 至 5.0V
- 下行转换
 - 1.8V V_{CC} 时,3.3V 至 1.8V
 - 2.5V V_{CC} 时,3.3V 至 2.5V
 - 3.3V V_{CC} 时, 5.0V 至 3.3V
- 逻辑输出以 Vcc 为基准
- 输出驱动
 - 5.0V 时, 8.0mA 的输出驱动
 - 3.3V 时, 7.0mA 的输出驱动
 - 1.8V 时, 3.0mA 的输出驱动
- 3.3V V_{CC} 时,频率高达 50MHz
- 输入引脚可耐受 5.0V 电压
- -40°C 至 125°C 工作温度范围
- 锁断性能超过 250mA 符合 JESD 17 规范
- 静电放电 (ESD) 性能测试符合 JESD 22 规范
 - 2000V 人体模型 (A114-B, II 类)
 - 200V 机器模型 (A115-A)
 - 1000V 充电器件模型 (C101)
- 支持标准逻辑引脚分配
- 与 AUP1G 和 LVC1G 系列兼容的 CMOS 输出 B
- (1) 请参考更低 V_{CC} 条件下的 V_{IH}/V_{IL} 和输出驱动。

2 应用范围

- 工业用控制器
- 电信
- 便携式应用
- 服务器
- 个人电脑和笔记本电脑
- 汽车

3 说明

SN74LV1T125 是一款具有较宽电压范围的低压 CMOS 门逻辑电路,用于工业、便携、电信和汽车应用。 输出电平以电源电压为基准,并且能够支持 1.8V/2.5V/3.3V/5V CMOS 电平。

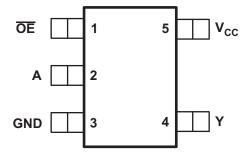
采用了更低阀值电路来设计此输入,以便匹配 V_{CC} = 3.3V 时的 1.8V 输入逻辑,并且可被用于 1.8V 至 3.3V 电平上行转换。此外,5V 容限输入引脚可实现下行转换(例如, V_{CC} = 2.5V 时的 3.3V 至 2.5V 输出转换)。 1.8V 至 5.5V 的宽 V_{CC} 范围可使所需输出电平的生成接至控制器或处理器。

SN74LV1T125 被设计成具有 8mA 的电流驱动能力, 以减少由高驱动输出导致的线路反射、过冲和下冲。

器件信息

订货编号	封装	封装尺寸
SN74LV1T125DBVR	小外形尺寸晶体管 封装 (SOT)-23 (5)	2.90mm x 1.60mm
SN74LV1T125DCKR	SC70 (5)	2.00mm x 1.25mm

DCK or DBV PACKAGE (TOP VIEW)



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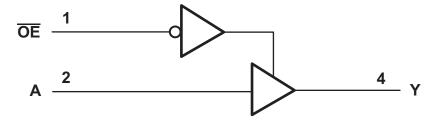
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INPU (Lower Leve	OUTPUT (V _{CC} CMOS)	
OE ⁽¹⁾	А	Y
L	Н	Н
L	L	L
Н	X	Z

(1) Not recommend to floating OE pin for signal oscillation

SUPPLY Vcc = 3.3V								
INPU (Lower Leve	-	OUTPUT (V _{CC} CMOS)						
Α	В	Υ						
VIH(min) = VIL(max) =		VOH(min) = 2.9 V VOL(max)= 0.2 V						

4.1 Logic Diagram



Switching Characteristics at 50 MHz

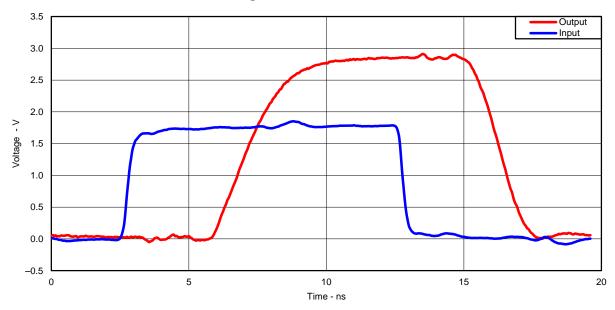
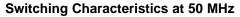


Figure 1. Excellent Signal Integrity (1.8V to 3.3V at 3.3V V_{CC})

Logic Diagram (continued)



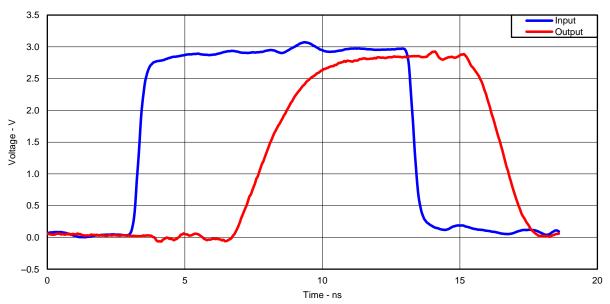


Figure 2. Excellent Signal Integrity (3.3V to 3.3V at 3.3V V_{CC})

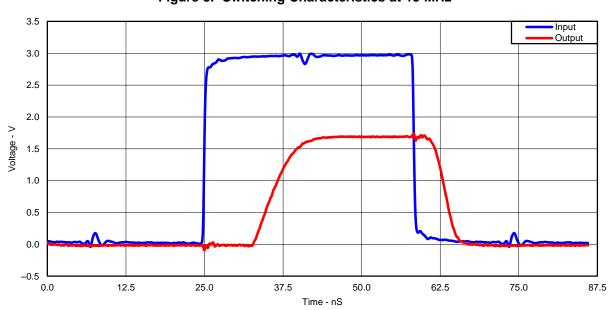


Figure 3. Switching Characteristics at 15 MHz

Figure 4. Excellent Signal Integrity (3.3V to 1.8V at 1.8V V_{CC})

4.2 Typical Design Examples

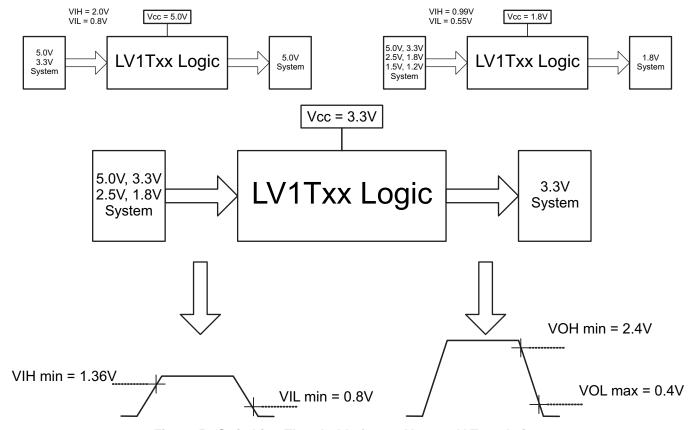


Figure 5. Switching Thresholds for 1.8-V to 3.3-V Translation

4.3 Absolute Maximum Ratings(1)

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V_{CC}	Supply voltage range	-0.5	7.0	V	
V_{I}	Input voltage range (2)		-0.5	7.0	V
.,	Voltage range applied to	-0.5	4.6	V	
Vo	Voltage range applied to	-0.5	V _{CC} + 0.5	V	
I _{IK}	Input clamp current	V ₁ < 0		-20	mA
I _{OK}	Output clamp current	$V_O < 0$ or $V_O > V_{CC}$		±20	mA
Io	Continuous output curren	t		±25	mA
	Continuous current through	gh V _{CC} or GND		±50	mA
0	Package thermal	DBV package		206	°C/W
θ_{JA}	impedance ⁽³⁾	DCK package		252	· C/VV
T _{stg}	Storage temperature rang	ge	-65	150	ů

⁽¹⁾ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

4.4 Recommended Operating Conditions⁽¹⁾

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT	
V_{CC}	Supply voltage		1.6	5.5	V	
V_{I}	Input voltage		0	5.5	V	
V_{O}	Output voltage		0	V_{CC}	V	
		V _{CC} = 1.8 V		-3.0		
	High-level output	V _{CC} = 2.5 V		-5.0	A	
I _{OH}	current	V _{CC} = 3.3 V		-7.0	mA	
		V _{CC} = 5.0 V		-8.0		
		V _{CC} = 1.8 V		3.0		
	Low-level output	V _{CC} = 2.5 V		5.0	^	
I _{OL}	current			7.0	mA	
		V _{CC} = 5.0 V		8.0		
		V _{CC} = 1.8 V		20		
Δt/Δν	Input transition rise or fall rate			20	ns/V	
	idii idio	V _{CC} = 5.0 V		20		
T _A	Operating free-air temp	perature	-40	125	°C	

⁽¹⁾ All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

⁽²⁾ The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.

⁽³⁾ The package thermal impedance is calculated in accordance with JESD 51-7.

4.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST COMPITIONS	V	T _A	= 25°C		T _A = -40°C to 125°C		UNIT			
	PARAMETER	TEST CONDITIONS	V _{cc}	MIN	TYP	MAX	MIN	MAX	UNII			
			$V_{CC} = 1.65 \text{ V to } 1.8 \text{ V}$	0.95			1.0					
			V _{CC} = 2.0 V	0.99			1.03					
			V_{CC} = 2.25 V to 2.5 V	1.145			1.18					
.,	High-level input		V _{CC} = 2.75 V	1.22			1.25		.,			
V _{IH}	voltage		_{VCC} = 3.0 V to 3.3 V	1.37			1.39		V			
			V _{CC} = 3.6 V	1.47			1.48					
			V _{CC} = 4.5 V to 5.0 V	2.02			2.03					
			V _{CC} = 5.5 V	2.1			2.11					
			V _{CC} = 1.65 V to 2.0 V			0.57		0.55				
	Low-level input		V _{CC} = 2.25 V to 2.75 V			0.75		0.71	.,			
/ _{IL} cow-level i			V _{CC} = 3.0 V to 3.6 V			0.8		0.65	V			
			V _{CC} = 4.5 V to 5.5 V			0.8		0.8				
		I _{OH} = -20 μA	1.65 V to 5.5 V	V _{CC} - 0.1			V _{CC} - 0.1					
			1.65 V	1.28			1.21					
		$I_{OH} = -2.0 \text{ mA}$	1.8 V	1.5			1.45		V			
		$I_{OH} = -3.0 \text{ mA}$	2.3 V	2.0			1.93					
		$I_{OH} = -3.0 \text{ mA}$	2.5 V	2.25			2.15		1			
/ _{OH}		$I_{OH} = -3.0 \text{ mA}$		2.78			2.7					
0		I _{OH} = -5.5 mA	3.0 V	2.6			2.49					
		I _{OH} = -5.5 mA	3.3 V	2.9			2.8		1			
		I _{OH} = -4.0 mA		4.2			4.1		V			
		$I_{OH} = -8.0 \text{ mA}$	4.5 V	4.1			3.95					
		I _{OH} = -8.0 mA	5.0 V	4.6			4.5					
		I _{OL} = 20 μA	1.65 V to 5.5 V			0.1		0.1				
		I _{OL} = 2.0 mA	1.65 V			0.2		0.25				
		I _{OH} = 3.0 mA	2.3 V			0.15		0.2				
V _{OL}		I _{OL} = 3.0 mA				0.11		0.15	V			
· OL		I _{OL} = 5.5 mA	3.0 V			0.21		0.252				
		I _{OL} = 4.0 mA				0.15		0.2				
		I _{OL} = 8.0 mA	4.5 V			0.3		0.35				
1	A input	V _I = 0 V or V _{CC}	0 V, 1.8 V, 2.5 V, 3.3 V, 5.5 V			0.1		±1.0	μΑ			
			5.0 V			1.0		10.0				
		$V_{I} = 0 \text{ V or } V_{CC}; I_{O} = 0;$	3.3 V			1.0		10.0				
СС		Open on loading V_{CC} , V_{CC} , V_{CC} , V_{CC}	2.5 V			1.0		10.0	μΑ			
			1.8 V			1.0		10.0	-			
		One input at 0.3 V or 3.4 V Other inputs at 0 or V _{CC} , I _O = 0	5.5 V			1.35		1.5	mA			
∆I _{CC}		One input at 0.3 V or 1.1 V Other inputs at 0 or V_{CC} , $I_O = 0$				10.0		10.0	μΑ			
C _i		V _I = V _{CC} or GND	3.3 V		2.0	10.0	2.0	10.0	pF			
C _o		$V_O = V_{CC}$ or GND	3.3 V		2.5		2.5		pF			

4.6 Switching Characteristics

over operating free-air temperature range (unless otherwise noted)

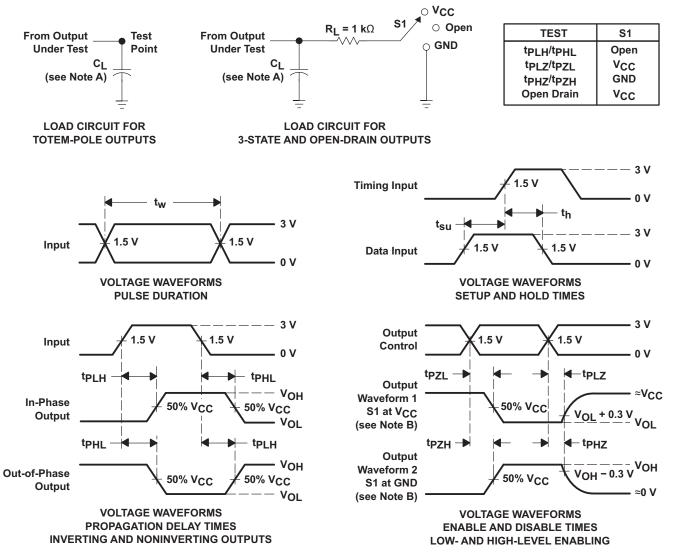
DADAMETED	FROM	то	FREQUENCY	.,		T _A = 25°0	;	$T_A = -65^{\circ}C \text{ to } 1$	25°C													
PARAMETER	(INPUT)	(OUTPUT)	(TYP)	V _{cc}	CL	MIN TYP	MAX	MIN TYP	MAX	UNIT												
				5.0 V	15 pF	2.7	5.5	3.4	6.5													
			DC to 50 MHz	5.0 V	30 pF	3.0	6.5	4.1	7.5	ns												
			DC 10 50 MHZ	3.3 V	15 pF	4.0	7.0	5.0	8.0													
	A my I Im	Υ			30 pF	4.9	8.0	6.0	9.0	ns												
t _{pd}	Any In	Y	DO : 05 MIL	2.5 V	15 pF	5.8	8.5	6.8	9.5													
			DC to 25 MHz	2.5 V	30 pF	6.5	9.5	7.5	10.5	ns												
			DC to 15 MHz	1.8 V	15 pF	10.5	13.0	11.8	14.0	ns												
			DC to 15 MHz	1.0 V	30 pF	12.0	14.5	12.0	15.5	115												
				5.0 V	15 pF	3.0	5.0	3.5	6.0	no												
			DC to 50 MHz DC to 25 MHz DC to 15 MHz	DC to 25 MHz	DC to 50 MHz	DC to 50 MHz	DC to 50 MHz	DC to 50 MHz	DC to 50 MHz		5.0 V	30 pF	4.3	6.5	4.9	7.5	ns					
										DO TO SO IVITIZ	DO TO SO IVITIZ	DC to 30 MHz	DC 10 30 WI 12	DC 10 30 WI 12	DC 10 30 WI 12	DC 10 30 WH 12	DC 10 30 WI 12	DC 10 30 WI 12	DC 10 30 WI 12	DO TO 30 IVITA	3.3 V	15 pF
	OE	Y			3.3 V	30 pF	5.0	8.0	6.5	9.0	ns											
t _{PZH} , t _{PZL}	OE	r			2.5 V	15 pF	5.5	8.0	6.1	9.0	ns											
					2.5 V	30 pF	7.0	10.0	8.5	11.0	115											
					DC to 15 MHz	DC to 15 MHz	DC to 15 MHz	DC to 15 MHz	DC to 15 MHz	DC to 15 MHz	DC to 15 MU-	DC to 15 MU	1.8 V	15 pF	9.0	12.0	9.85	13.0	ns			
											1.0 V	30 pF	12.5	15.0	13.5	16.0	115					
				5.0 V	15 pF	4.2	6.5	4.5	7.0	ns												
			DC to 50 MHz	3.0 V	30 pF	4.8	8.0	5.0	8.5	115												
			DC to 50 MHz	3.3 V	15 pF	4.5	7.0	5.0	8.0	ne												
	OE	Υ		3.3 V	30 pF	5.0	8.0	5.5	9.0	ns												
t_{PHZ} , t_{PLZ}	OE .	ī	DC to 35 MHz	2.5 V	15 pF	5.0	11.0	6.0	9.0	20												
			DC to 25 MHz	2.3 V	30 pF	6.0	9.0	7.0	10.0	ns												
			DC to 15 MHz	1.8 V	15 pF	8.0	10.0	8.5	11.0													
			DC to 15 MIHZ	1.0 V	30 pF	8.5	11.0	9.5	12.0	ns												

4.7 Operating Characteristics

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	V _{cc}	TYP	UNIT
			1.8 V ± 0.15 V	14	
	Dever dissination consistence	f 4 MHz and 40 MHz	$2.5 \text{ V} \pm 0.2 \text{ V}$	14	pF
C _{pd}	Power dissipation capacitance	f = 1 MHz and 10 MHz	$3.3 \text{ V} \pm 0.3 \text{ V}$	14	рі
			5.0 V ± 0.5 V	14	

5 Parameter Measurement Information



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 1 MHz, Z_O = 50 Ω , $t_f \leq$ 3 ns. $t_f \leq$ 3 ns.
- D. The outputs are measured one at a time, with one input transition per measurement.
- E. All parameters and waveforms are not applicable to all devices.

Figure 6. Load Circuit and Voltage Waveforms

Parameter Measurement Information (continued)

5.1 More Product Selection

DEVICE	PACKAGE	DESCRIPTION
SN74LV1T00	DCK, DBV	2-Input Positive-NAND Gate
SN74LV1T02	DCK, DBV	2-Input Positive-NOR Gate
SN74LV1T04	DCK, DBV	Inverter Gate
SN74LV1T08	DCK, DBV	2-Input Positive-AND Gate
SN74LV1T125	DCK, DBV, DPW	Single Buffer Gate
SN74LV1T14	DCK, DBV	Single Schmitt-Trigger Inverter Gate
SN74LV1T32	DCK, DBV	2-Input Positive-OR Gate
SN74LV1T86	DCK, DBV	Single 2-Input Exclusive-Or Gate
SN74LV1T125	DCK, DBV	Single Buffer Gate with 3-state Output
SN74LV1T125	DCK, DBV	Single Buffer Gate with 3-state Output
SN74LV4T125	RGY, PW	Quadruple Bus Buffer Gate With 3-State Outputs

6 器件和文档支持

6.1 Trademarks

All trademarks are the property of their respective owners.

6.2 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

6.3 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms and definitions.

7 机械,封装和可订购信息

下列封装信息和附录反映了针对指定器件可提供的最新数据。 这些数据会在无通知且不对本文档进行修订的情况下 发生改变。

10-Dec-2020

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty		Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
SN74LV1T125DBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(NEZ3, NEZJ, NEZS)	Samples
SN74LV1T125DBVRG4	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	NEZ3	Samples
SN74LV1T125DCKR	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(WZ3, WZJ, WZS)	Samples
SN74LV1T125DCKRG4	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM		WZ3	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

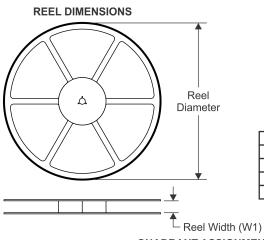
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

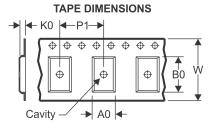
Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and

TAPE AND REEL INFORMATION





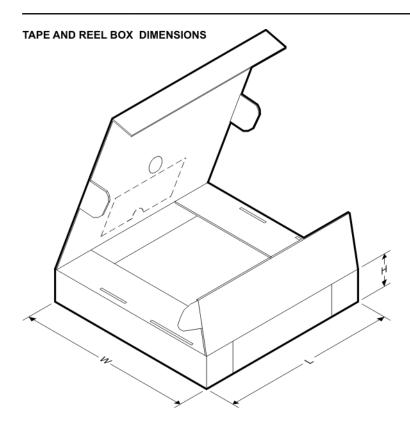
	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LV1T125DBVR	SOT-23	DBV	5	3000	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
SN74LV1T125DBVR	SOT-23	DBV	5	3000	178.0	9.2	3.3	3.23	1.55	4.0	8.0	Q3
SN74LV1T125DBVR	SOT-23	DBV	5	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
SN74LV1T125DBVRG4	SOT-23	DBV	5	3000	178.0	9.2	3.3	3.23	1.55	4.0	8.0	Q3
SN74LV1T125DCKR	SC70	DCK	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74LV1T125DCKR	SC70	DCK	5	3000	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74LV1T125DCKR	SC70	DCK	5	3000	180.0	8.4	2.47	2.3	1.25	4.0	8.0	Q3
SN74LV1T125DCKRG4	SC70	DCK	5	3000	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3

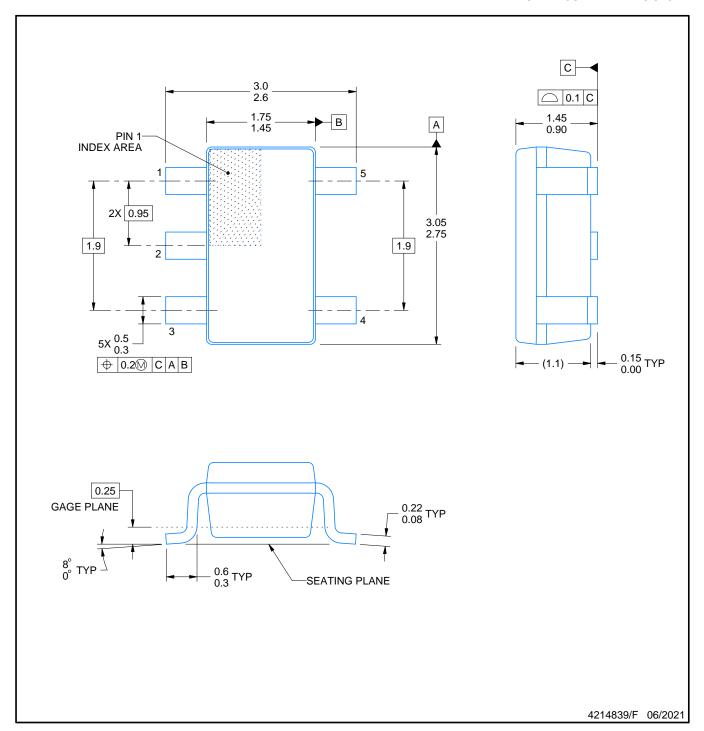


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LV1T125DBVR	SOT-23	DBV	5	3000	202.0	201.0	28.0
SN74LV1T125DBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74LV1T125DBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74LV1T125DBVRG4	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74LV1T125DCKR	SC70	DCK	5	3000	180.0	180.0	18.0
SN74LV1T125DCKR	SC70	DCK	5	3000	180.0	180.0	18.0
SN74LV1T125DCKR	SC70	DCK	5	3000	202.0	201.0	28.0
SN74LV1T125DCKRG4	SC70	DCK	5	3000	180.0	180.0	18.0



SMALL OUTLINE TRANSISTOR



NOTES:

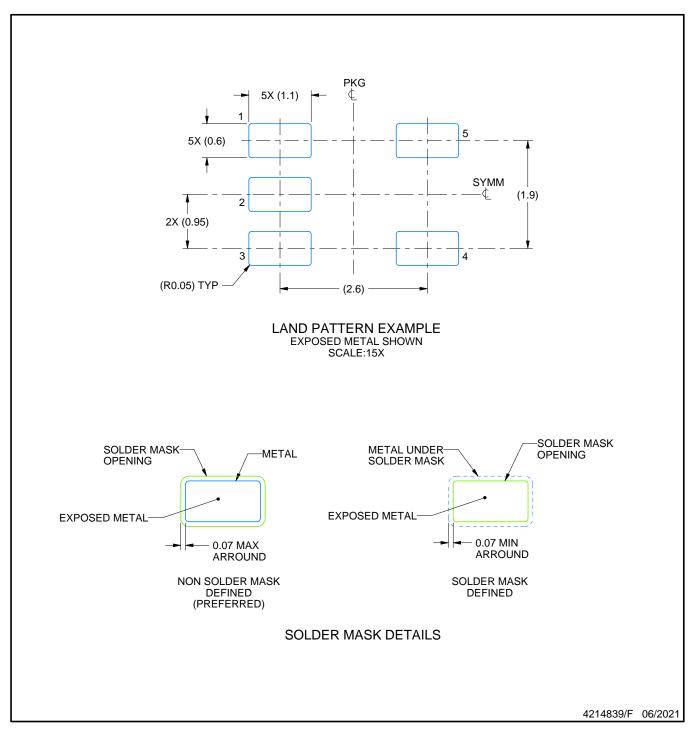
- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. Reference JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.

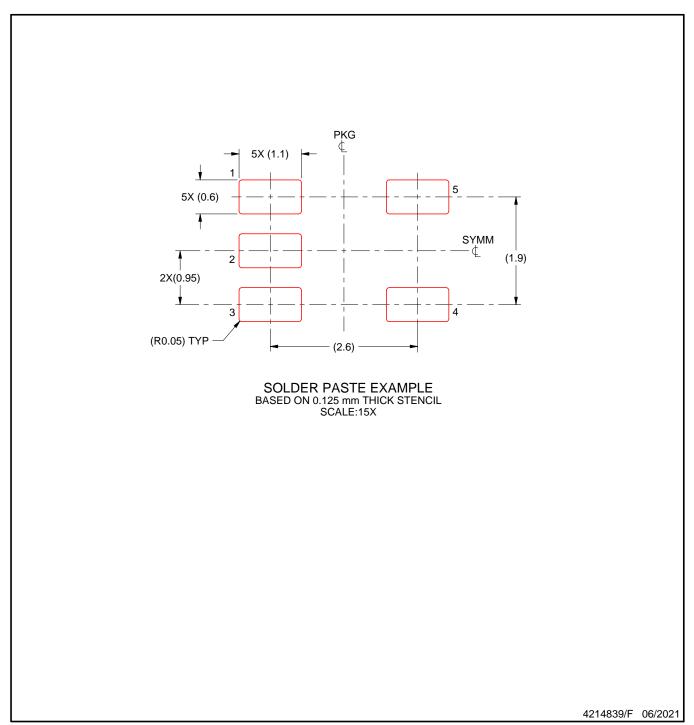
SMALL OUTLINE TRANSISTOR



NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

SMALL OUTLINE TRANSISTOR



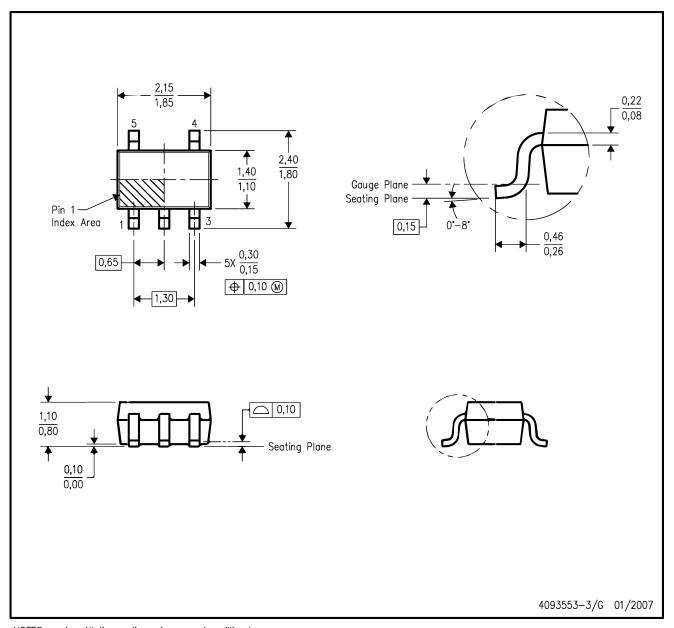
NOTES: (continued)

^{7.} Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

^{8.} Board assembly site may have different recommendations for stencil design.

DCK (R-PDSO-G5)

PLASTIC SMALL-OUTLINE PACKAGE

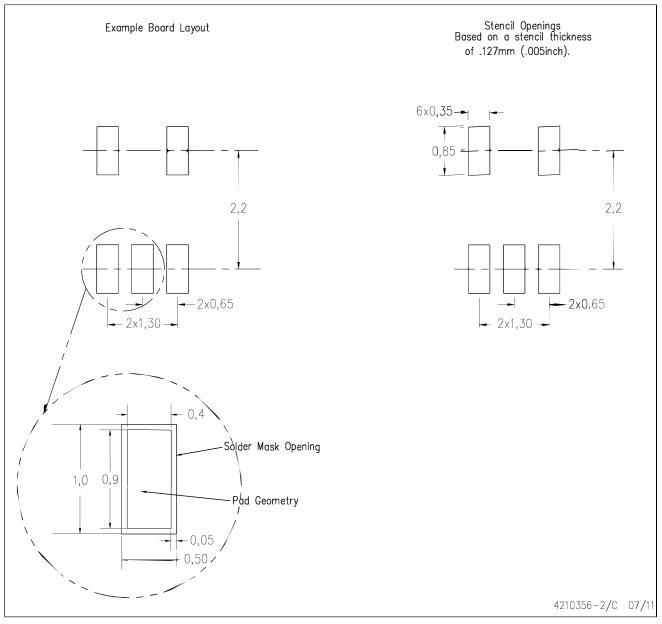


NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
- D. Falls within JEDEC MO-203 variation AA.

DCK (R-PDSO-G5)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.